

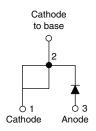
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 16 A



TO-247AC modified



PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
I _{F(AV)}	16 A
V_{R}	1200 V
V _F at I _F	2.3 V
t _{rr} typ.	30 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current. the VS-HFA16PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V_{R}		1200	V				
Maximum continuous forward current	I _F	T _C = 100 °C	16					
Single pulse forward current	I _{FSM}		190	Α				
Maximum repetitive forward current	I _{FRM}		64					
Maximum nauca dissination	Б	T _C = 25 °C	151	W				
Maximum power dissipation	P_{D}	T _C = 100 °C	60] vv				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				



VS-HFA16PB120PbF, VS-HFA16PB120-N3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage		I _F = 16 A		-	2.5	3.0	V		
	V_{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93			
		I _F = 16 A, T _J = 125 °C		=	2.3	2.7			
Maximum reverse	1	V _R = V _R rated	Coo fig. 0	-	0.75	20			
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See fig. 2	-	375	2000	μΑ		
Junction capacitance	C _T	V _R = 200 V See fig. 3		=	27	40	pF		
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nΗ		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$) A/μs, V _R = 30 V	-	30	-			
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/μs V _R = 200 V	-	90	135	ns		
occ lig. 5, 10	t _{rr2}	T _J = 125 °C		-	164	245			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	5.8	10	A nC		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15			
Reverse recovery charge See fig. 7	Q _{rr1}	T _J = 25 °C		-	260	675			
	Q _{rr2}	T _J = 125 °C		-	680	1838	IIC		
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	-	- A/μs		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	0.83				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-				
\\/aight			-	2.0	-	g			
Weight			-	0.07	-	OZ.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AC modified (JEDEC)		HFA16	SPB120	•			

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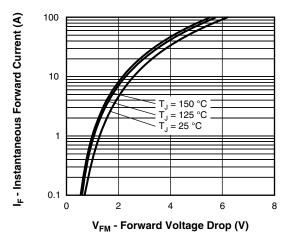


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

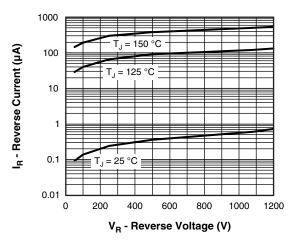


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

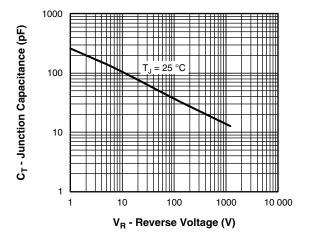


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

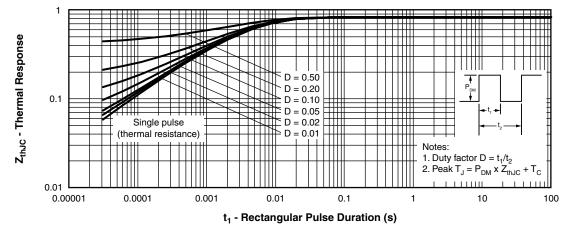


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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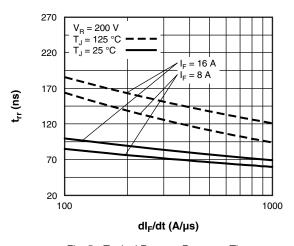


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)

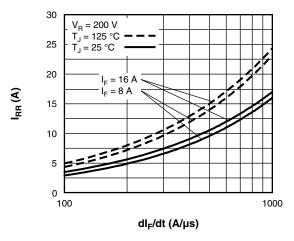


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

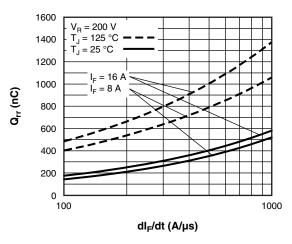


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

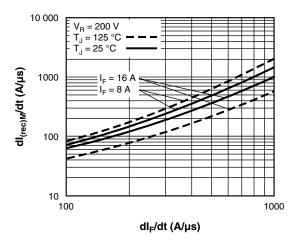


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

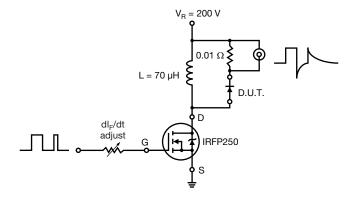
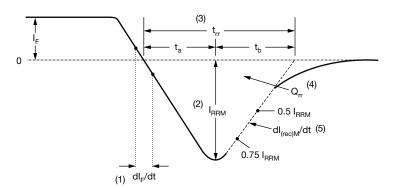


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA16PB120PbF, VS-HFA16PB120-N3

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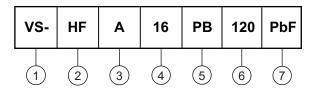
- (1) dl_F/dt rate of change of current through zero crossing
 - ough zero crossing and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

(4) Q_{rr} - area under curve defined by t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Electron irradiated
- Current rating (16 = 16 A)
- 5 PB = TO-247AC modified
- 6 Voltage rating: (120 = 1200 V)
- 7 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA16PB120PbF	25	500	Antistatic plastic tube					
VS-HFA16PB120-N3	25	500	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95541						
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255						
	TO-247AC modified -N3	www.vishay.com/doc?95442						



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NOTES

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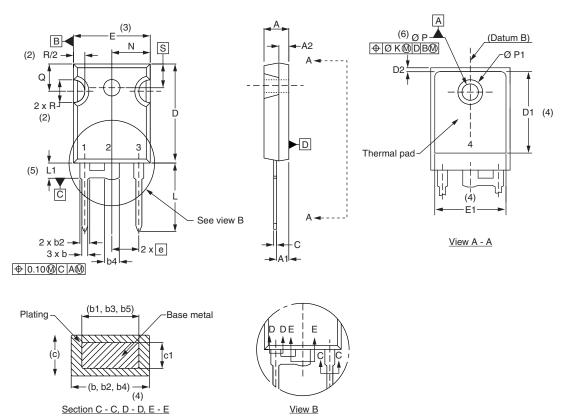
MAX. 0.051 0.625

0.634 0.169

0.144 0.275 0.224 0.216

TO-247 modified

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIN	IETERS	INC	HES			
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIBUL	MIN.	MAX.	MIN.	MAX		
Α	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.05		
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.62		
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-		
b	0.99	1.40	0.039	0.055			е	5.46	5.46 BSC		BSC		
b1	0.99	1.35	0.039	0.053			ØK	2.54		0.0)10		
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.63		
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.16		
b4	2.59	3.43	0.102	0.135			N	7.62 BSC		7.62 BSC		0	.3
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.14		
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.27		
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.22		
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.21		
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC		

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c



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